DGG OR DL PACKAGE

(TOP VIEW)

SCES080C - JULY 1996 - REVISED FEBRUARY 1999

- **Member of the Texas Instruments** *Widebus*™ Family
- **EPIC** ™ (Enhanced-Performance Implanted **CMOS) Submicron Process**
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per **JESD 17**
- Bus Hold on Data Inputs Eliminates the **Need for External Pullup/Pulldown**
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages

description

This 18-bit universal bus transceiver is designed for 1.65-V to 3.6-V V_{CC} operation.

Data flow in each direction is controlled by (OEAB and OEBA) output-enable clock-enable (CLKENBA) inputs. For the A-to-B data flow, the data flows through a single buffer. The B-to-A data can flow through a four-stage pipeline register path, or through a single register path, depending on the state of the select (SEL) input.

Data is stored in the internal registers on the low-to-high transition of the clock (CLK) input, provided that the appropriate CLKENBA input is low. The B-to-A data transfer is synchronized with CLK.

56 GND GND [OEAB 2 55 SEL A1 Π 3 54 **∏** B1 GND 14 53 GND A2 🛮 5 52 N B2 51 B3 A3 🛮 6 50 [] V_{CC} V_{CC} **∐** 7 A4 🛮 8 49 🛮 B4 A5 🛮 9 48 B5 A6 🛮 10 47 B6 46 GND GND II 11 A7 | 12 45 **∏** B7 A8 🛮 13 44 B8 А9 П 14 43 **∏** B9 42 **∏** B10 A10 ∏ 15 A11 16 41 B11 А12 П 17 40 П в12 GND **1** 18 39 | GND 38 B13 A13 19 А14 П **∏** B14 20 37 A15 21 36 **∏** B15 V_{CC} **□** 22 35 V_{CC} A16 23 34 🛮 B16 33 **∏** B17 A17 | 24 GND ∏25 32 | GND A18 **∏** 26 31 N B18 OEBA **∏** 27 30 T CLK 29 | GND

To ensure the high-impedance state during power up or power down, $\overline{\sf OE}$ should be tied to V $_{\sf CC}$ through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16524 is characterized for operation from –40°C to 85°C.



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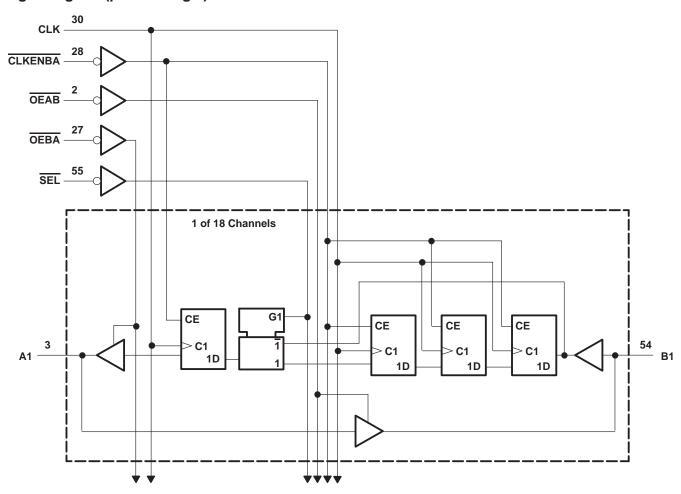


FUNCTION TABLE B-TO-A STORAGE ($\overline{OEBA} = L$)

	OUTPUT					
CLKENBA	CLK	SEL	SEL B			
Н	Х	Х	Х	A ₀ †		
L	\uparrow	Н	L	L		
L	\uparrow	Н	Н	Н		
L	\uparrow	L	L	L‡		
L	\uparrow	L	Н	H‡		

[†]Output level before the indicated steady-state input

logic diagram (positive logic)





conditions were established

‡ Four positive CLK edges are needed to propagate data from B to A when SEL is low.

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply	voltage range, V _{CC}	
Input vo	oltage range, V _I : Except I/O ports (see Note 1)	
	I/O ports (see Notes 1 and 2)	
Output	voltage range, V _O (see Notes 1 and 2)	$-0.5 \text{ V to V}_{CC} + 0.5 \text{ V}$
Input cl	amp current, I _{IK} (V _I < 0)	–50 mA
Output	clamp current, I _{OK} (V _O < 0)	–50 mA
Continu	uous output current, IO	±50 mA
Continu	uous current through each V _{CC} or GND	±100 mA
Packag	ge thermal impedance, θ_{JA} (see Note 3): DGG pack	kage 81°C/W
	DL packa	ge 74°C/W
Storage	e temperature range, T _{stg}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

- 2. This value is limited to 4.6 V maximum.
- 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
Vcc	Supply voltage		1.65	3.6	V	
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	0.65 × V _{CC}			
V_{IH}	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V	
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2			
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		0.35 × V _{CC}	V	
V_{IL}	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7		
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		0.8		
VI	Input voltage		0	VCC	V	
٧o	Output voltage		0	Vcc	V	
		V _{CC} = 1.65 V		-4		
la	High-level output current	V _{CC} = 2.3 V		-12	mA	
ЮН		V _{CC} = 2.7 V		-12		
		V _{CC} = 3 V		-24		
		V _{CC} = 1.65 V		4		
la.	Low-level output current	V _{CC} = 2.3 V		12	^	
lOL		V _{CC} = 2.7 V		12	mA	
		V _{CC} = 3 V		24		
Δt/Δν	Input transition rise or fall rate			10	ns/V	
TA	Operating free-air temperature		-40	85	°C	

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



SN74ALVCH16524 18-BIT REGISTERED BUS TRANSCEIVER WITH 3-STATE OUTPUTS

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PA	RAMETER	TEST C	ONDITIONS	Vcc	MIN	TYP [†]	MAX	UNIT	
		I _{OH} = -100 μA		1.65 V to 3.6 V	V _{CC} -0.	.2			
VOH	I _{OH} = -4 mA		1.65 V	1.2					
	I _{OH} = -6 mA	2.3 V	2						
			2.3 V	1.7			V		
	I _{OH} = -12 mA		2.7 V	2.2					
			3 V	2.4					
	I _{OH} = -24 mA	3 V	2						
		I _{OL} = 100 μA		1.65 V to 3.6 V			0.2		
		I _{OL} = 4 mA		1.65 V			0.45		
Mar.		I _{OL} = 6 mA	2.3 V			0.4	V		
VOL		I _{OL} = 12 mA	2.3 V			0.7	v		
		IOL = 12 IIIA	2.7 V			0.4			
		I _{OL} = 24 mA	3 V			0.55			
lį		$V_I = V_{CC}$ or GND		3.6 V			±5	μΑ	
		V _I = 0.58 V	1.65 V	25					
		V _I = 1.07 V	1.65 V	-25					
		V _I = 0.7 V	2.3 V	45					
I _{I(hold)}		V _I = 1.7 V	2.3 V	-45			μΑ		
		V _I = 0.8 V	3 V	75					
		V _I = 2 V	3 V	-75					
		$V_1 = 0 \text{ to } 3.6 \text{ V}^{\ddagger}$		3.6 V			±500		
loz§		$V_O = V_{CC}$ or GND		3.6 V			±10	μΑ	
ICC		$V_I = V_{CC}$ or GND,	IO = 0	3.6 V			40	μΑ	
∆ICC		One input at V _{CC} – 0.6 V,	Other inputs at V _{CC} or GND	3 V to 3.6 V			750	μΑ	
Ci	Control inputs	$V_I = V_{CC}$ or GND		3.3 V		3		pF	
C _{io}	A or B ports	$V_O = V_{CC}$ or GND		3.3 V		7		pF	

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

			V _{CC} = 1.8 V		$V_{CC} = 1.8 \text{ V}$ $V_{CC} = 2.5 \text{ V}$ $\pm 0.2 \text{ V}$		V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
fclock	Clock frequency			¶		120		125		150	MHz
t _W	Pulse duration, CLK high or low		¶		3.2		3.2		3		ns
		B data before CLK↑	¶		1.5		1.2		1.1		ns
t _{su}	Setup time	SEL before CLK↑	¶		2.7		2.4		2.1		
	CLKENBA before CLK↑	¶		2.7		2.6		2			
t _h Hold time	B data after CLK↑	¶		1		0.6		1.2			
	SEL after CLK↑	¶		0.5		0.2		0.8		ns	
	CLKENBA after CLK↑	¶		0.1		0.1		0.3			

This information was not available at the time of publication.



[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C. ‡ This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

[§] For I/O ports, the parameter IOZ includes the input leakage current.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	VCC =	1.8 V	V _{CC} =	2.5 V 2 V	VCC =	2.7 V	V _{CC} =	3.3 V 3 V	UNIT
	(1141-01)	(0011 01)	MIN	TYP	MIN	MAX	MIN	MAX	MIN	MAX	
f _{max}			†		120		125		150		MHz
^t pd	А	В		†	1	3.9		3.8	1	3.2	
	CLK	А		†	1	6.1		6.2	1	5.2	ns
t _{en}	OEAB or OEBA	A or B		†	1	6.1		6.1	1	5.1	ns
^t dis	OEAB or OEBA	A or B		†	1	6.3		5.4	1	4.9	ns

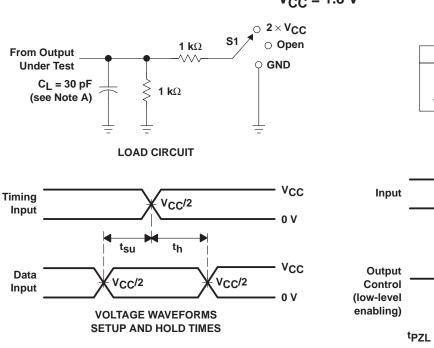
[†] This information was not available at the time of publication.

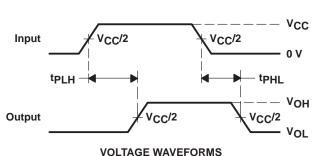
operating characteristics, $T_A = 25^{\circ}C$

PARAMETER		TEST CONDITIONS	V _{CC} = 1.8 V V _{CC} = 2.5 V		V _{CC} = 3.3 V	UNIT		
		TEST CONDITIONS	TYP	TYP	TYP	ONIT		
	Power dissipation	Outputs enabled	C ₁ = 50 pF. f = 10 MHz	†	160	160	pF	
Cpd	capacitance	Outputs disabled	$C_L = 50 \text{ pF}, f = 10 \text{ MHz}$	†	160	160	þг	

[†] This information was not available at the time of publication.

PARAMETER MEASUREMENT INFORMATION V_{CC} = 1.8 V





PROPAGATION DELAY TIMES

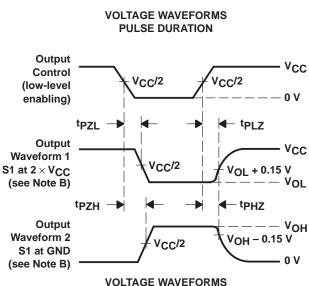
 $\begin{array}{c|c} \textbf{TEST} & \textbf{S1} \\ \hline & t_{pd} & \textbf{Open} \\ \textbf{tPLZ/tPZL} & \textbf{2} \times \textbf{V}_{CC} \\ \textbf{tPHZ/tPZH} & \textbf{GND} \\ \end{array}$

V_{CC}/2

VCC

0 V

V_{CC}/2



ENABLE AND DISABLE TIMES

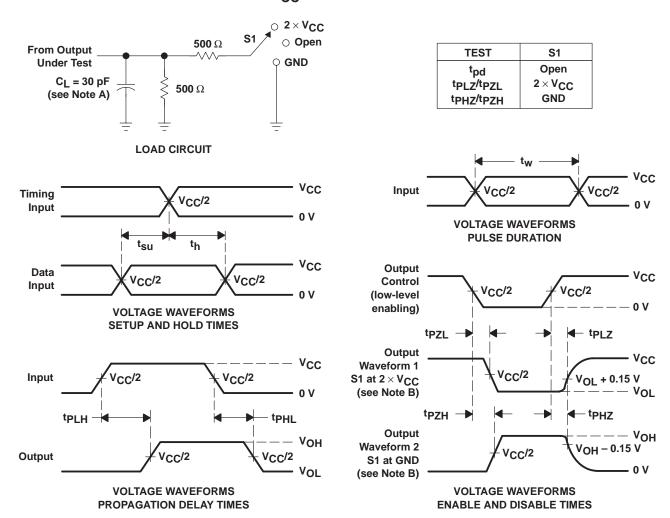
NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \ \Omega$, $t_f \leq$ 2 ns. $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpl 7 and tpH7 are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tplH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$

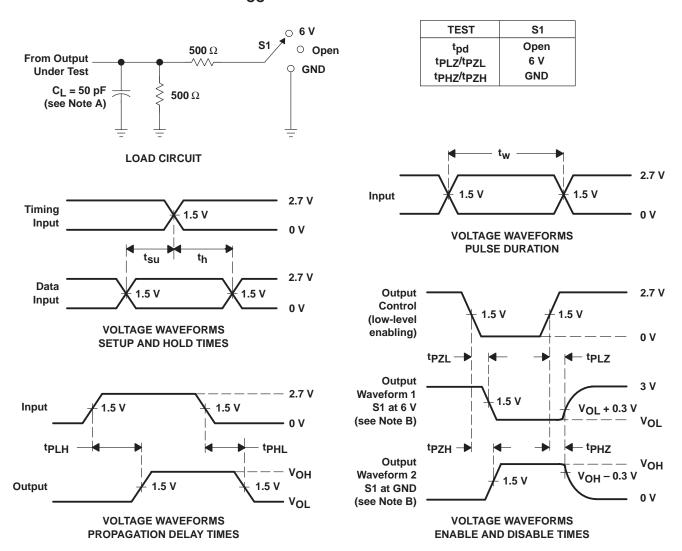


NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_Q = 50 Ω , $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.7 V AND 3.3 V \pm 0.3 V



- NOTES: A. C_I includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq$ 2.5 ns. $t_f \leq$ 2.5 ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpl 7 and tpH7 are the same as tdis.
 - F. tpZL and tpZH are the same as ten.
 - G. tpLH and tpHL are the same as tpd.

Figure 3. Load Circuit and Voltage Waveforms



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